





参考資料





TUSB211A JAJSR79 - SEPTEMBER 2023

TUSB211A USB 2.0 480Mbps 高速シグナル・コンディショナ

1 特長

- 広い電源電圧範囲:2.3~6.5V
- USB 切断時およびシャットダウン時の非常に低い消費
- USB 2.0 High-Speed 信号のコンディショニングを提
- USB 2.0、OTG 2.0、BC 1.2 に対応
- Low-Speed、Full-Speed、High-Speed 信号処理の
- 特定のホストやデバイスに非依存
- 最大 5m のケーブル長をサポート
 - 外付けのプルダウン抵抗により 4 つの信号 EQ (エ ッジ・ブーストと DC ブースト) 設定を選択可能
- 2 つの TUSB211A デバイスを使って最大 10m のケ ーブル長に対応
- スケーラブルなソリューション 損失が大きいアプリケ ーションに対応するため、デバイスをデイジー・チェー ン接続可能
- TUSB211、212、214、216、217A (3.3V) とピン互換

2 アプリケーション

- ラップトップ、デスクトップまたはドッキング・ステーション
- 携帯電子機器
- タブレット
- 携帯電話
- テレビ
- アクティブ・ケーブル、延長ケーブル、バックプレーン

3 概要

TUSB211A は第3世代 USB 2.0 High Speed 信号コン ディショナーで、伝送チャネルでの AC 損失 (容量性負荷 による) および DC 損失 (抵抗損失による) を補償するよう に設計されています。

TUSB211A には、エッジ・ブースタにより USB 2.0 High Speed 信号の遷移エッジを高速化し、DC ブースト機能に より静的電圧レベルを上げる特許取得済みの設計が採用 されています。

また、TUSB211A はプリイコライゼーション機能を備えて いるため、長いケーブルを使用するアプリケーションで ISI (符号間干渉) ジッタを補償できます。USB Low Speed および Full Speed 信号特性は、TUSB211A による影響 を受けません。

TUSB211A は、パケット・タイミングを変更せず、また、伝 搬遅延やレイテンシを追加せずに、信号品質を向上させ ることができます。

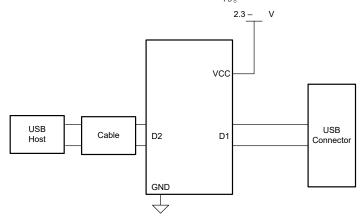
TUSB211A により、最長 5 メートルのケーブルを使用した システムで、USB 2.0 High Speed 近端アイ・コンプライア ンスに合格することが可能になります。

TUSB211A は、USB On-The-Go (OTG) および Battery Charging (BC) プロトコルにも対応しています。

製品情報

部品番号	パッケージ ⁽¹⁾	動作温度 (T _A) ℃	本体サイズ (公称)(2)
TUSB211A	RWB	0~70	1.6mm × 1.6mm
TUSB211AI	(X2QFN, 12)	-40~85	1.011111 ~ 1.0111111

- 利用可能なパッケージについては、データシートの末尾にある注 文情報を参照してください。
- 本体サイズ (長さ×幅) は公称値であり、ピンは含まれていませ (2) λ_{\circ}



概略回路図



Table of Contents

1 特長	1	7.2 Functional Block Diagram	7
2アプリケーション		7.3 Feature Description	<mark>7</mark>
3 概要		7.4 Device Functional Modes	<mark>7</mark>
4 Revision History		8 Application and Implementation	9
5 Pin Configuration and Functions		8.1 Application Information	9
6 Specifications		8.2 Typical Application	9
6.1 Absolute Maximum Ratings		8.3 Power Supply Recommendations	15
6.2 ESD Ratings		8.4 Layout	15
6.3 Recommended Operating Conditions		9 Device and Documentation Support	17
6.4 Thermal Information		9.1ドキュメントの更新通知を受け取る方法	17
6.5 Electrical Characteristics	5	9.2 サポート・リソース	17
6.6 Switching Characteristics		9.3 Trademarks	17
6.7 Timing Requirements		9.4 静電気放電に関する注意事項	17
6.8 Typical Characteristics		9.5 用語集	
7 Detailed Description		10 Mechanical, Packaging, and Orderable	
7.1 Overview		Information	17

4 Revision History

DATE	REVISION	NOTES
September 2023	*	Initial Release



5 Pin Configuration and Functions

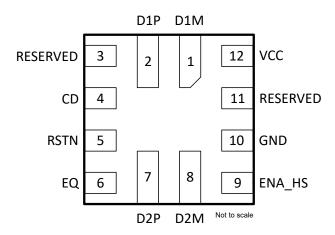


図 5-1. TUSB211A RWB 12-Pin X2QFN (Top View)

表 5-1. Pin Functions

	致 5-1. First unctions					
PIN		TYPE(1)	INTERNAL	DESCRIPTION		
NAME NO.		1115.7	PULLUP/PULLDOWN	DECOMI NON		
EQ	6	I	N/A	USB High-speed EQ select via external pull down resistor. Both edge boost and DC boost are controlled by a single pin. Sampled upon power up. Does not recognize real time adjustments. Auto selects EQ LEVEL = 3 when left floating.		
RESERVED	11	ı	500 kΩ PU	Reserved pin for TI test purposes. Leave floating or connect external capacitor to GND for normal operation.		
ENA_HS	9	I/O	N/A	After reset: Output signal ENA_HS. Flag indicating that channel is in High-speed mode. Asserted upon: 1. Detection of USB-IF High-speed test fixture from an unconnected state followed by transmission of USB TEST_PACKET pattern. 2. Squelch detection following USB reset with a successful HS handshake [HS handshake is declared to be successful after single chirp J chirp K pair where each chirp is within 18 µs – 128 µs].		
D2P	7	I/O	N/A	USB High-speed positive port.		
D2M	8	I/O	N/A	USB High-speed negative port.		
GND	10	Р	N/A	Ground		
D1M	1	I/O	N/A	USB High-speed negative port.		
D1P	2	I/O	N/A	USB High-speed positive port.		
RESERVED	3	I/O	500 kΩ PU 1.8 MΩ PD	Reserved pin for TI test purposes. Leave floating for normal operation.		
VCC	12	Р	N/A	Supply power		
RSTN	5	I	500 kΩ PU 1.8 MΩ PD	Device disable/enable. Low – Device is at reset and in shutdown, and High - Normal operation. Recommend 0.1-µF external capacitor to GND to ensure clean power on reset if not driven. If the pin is driven, it must be held low until the supply voltage for the device reaches within specifications.		
CD	4	0	When RSTN asserted there is a 500 kΩ PD	After reset: Output CD. Flag indicating that a USB device is attached (connection detected). Asserted from an unconnected state upon detection of DP or DM pull-up resistor. De-asserted upon detection of disconnect.		
	1	I	1	1		

Product Folder Links: TUSB211A

(1) I = input, O = output, P = power



6 Specifications

6.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
Supply voltage range	VCC	-0.3	7	V
Voltage range USB data	DxP, DxM	-0.3	5.5	V
Voltage range on EQ pin	EQ	-0.3	1.98	V
Voltage range other pins	RSTN	-0.3	5.5	V
Storage temperature, T _{stg}		-65	150	°C
Maximum junction temperature, T _{J (max)}			125	°C

(1) Operation outside the Absolute Maximum Rating may cause permanent device damage. Absolute Maximum Rating do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Condition. If used outside the Recommended Operating Condition but within the Absolute Maximum Rating, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽²⁾	±2000	V
V _(ESD)	Liectiostatic discharge	Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽³⁾	±750	v

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	2.3	5	6.5	V
т	Operating free-air temperature (TUSB211A)	0	-	70	°C
I _A	Operating free-air temperature (TUSB211AI)	-40		85	°C
т	Junction temperature (TUSB211A)			85	°C
l J	Junction temperature (TUSB211AI)			105	°C
DxP, DxM	Voltage range USB data	0		3.6	V
EQ	Voltage range EQ pin	0		1.98	V
DIGITAL	Voltage range other pins (RSTN)	0		3.6	V

6.4 Thermal Information

	THERMAL METRIC (1)	RWB (X2QFN)	UNIT
	I DERWAL INETRIC (1)	12 PINS	ONII
$R_{\theta JA}$	Junction-to-ambient thermal resistance	137.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	62	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	67.2	°C/W
ΨЈТ	Junction-to-top characterization parameter	1.9	°C/W
ΨЈВ	Junction-to-board characterization parameter	67.3	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

 For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

Over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP (1)	MAX	UNIT
POWER						
I _{ACTIVE_HS}	High Speed Active Current	USB channel = HS mode. 480 Mbps traffic. V _{CC} supply stable, with EQ = Max		22	36	mA
I _{IDLE_HS}	High Speed Idle Current	USB channel = HS mode, no traffic. V _{CC} supply stable, EQ = Max		22	36	mA
I _{HS_SUSPEND}	High Speed Suspend Current	USB channel = HS Suspend mode. V _{CC} supply stable		0.75	1.4	mA
I _{FS}	Full-Speed Current	USB channel = FS mode, 12 Mbps traffic, V _{cc} supply stable		0.75	1.4	mA
I _{DISCONN}	Disconnect Power	Host side application. No device attachment.		0.80	1.4	mA
I _{SHUTDN}	Shutdown Power	RSTN driven low, V _{CC} supply stable		60	115	μΑ
CONTROL PIN L	EAKAGE					
I _{LKG_FS}	Pin failsafe leakage current for RSTN	V _{CC} = 0 V, pin at V _{IH, max}		10	15	μΑ
INPUT RSTN						
V _{IH}	High level input voltage		1.5		3.6	V
V _{IL}	Low-level input voltage		0		0.5	V
I _{IH}	High level input current	V _{IH} = 3.6 V, R _{PU} enabled			±15	μA
I _{IL}	Low level input current	V _{IL} = 0V, R _{PU} enabled			±20	μA
INPUT EQ	,					
R _{EQ_LVL0}	External pulldown resistor for EQ Level 0				160	Ω
R _{EQ_LVL1}	External pulldown resistor for EQ Level 1		1.5	1.8	2	kΩ
R _{EQ_LVL2}	External pulldown resistor for EQ Level 2		3.4	3.6	3.96	kΩ
R _{EQ_LVL3}	External pulldown resistor for EQ Level 3 to remove upper limit for resistor value, can be left open		7.5			kΩ
OUTPUTS CD, E	ENA_HS					
V _{OH}	High level output voltage for CD and ENA_HS	I _O = -50 μA, VCC >= 3.0 V	2.5			V
V _{OH}	High level output voltage for CD	I _O = -25 μA, VCC = 2.3 V	1.7			V
V _{OH}	High level output voltage for ENA_HS	I _O = -25 μA, VCC = 2.3 V	1.8			V
V _{OL}	Low level output voltage for CD and ENA_HS	Ι _Ο = 50 μΑ			0.3	V
DxP, DxM						
C _{IO_DXX}	Capacitance to GND	Measured with VNA at 240 MHz, V _{CC} supply stable, Redriver off		2.5		pF

⁽¹⁾ All typical values are at V_{CC} = 5 V, and T_A = 25°C.

6.6 Switching Characteristics

Over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP (1)	MAX	UNIT
DxP, DxM USB Signals						
F _{BR_DXX}	Bit Rate	USB channel = HS mode. 480 Mbps traffic. V _{CC} supply stable			480	Mbps
t _{R/F_DXX}	Rise/Fall time		100			ps

⁽¹⁾ All typical values are at V_{CC} = 5 V, and T_A = 25°C.

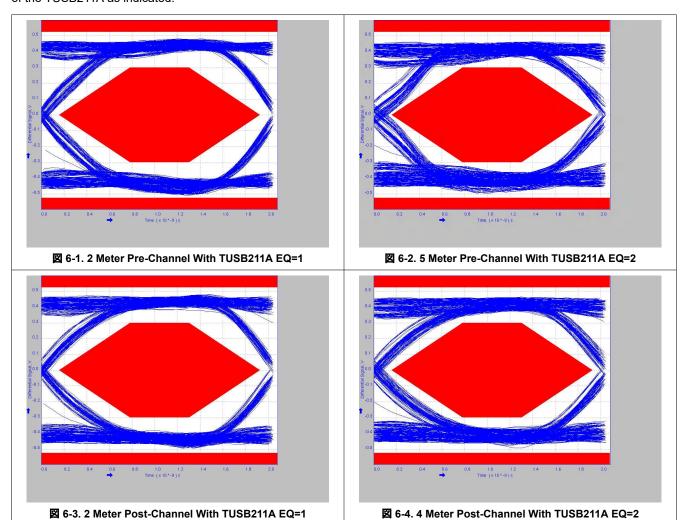


6.7 Timing Requirements

		MIN	NOM MAX	UNIT			
POWER UP TIMING							
T _{RSTN_PW}	Minimum width to detect a valid RSTN signal assert when the pin is actively driven low	100		μs			
T _{STABLE}	VCC must be stable before RSTN de-assertion	300		μs			
T _{READY}	Maximum time needed for the device to be ready after RSTN is deasserted.		500	μs			
T _{RAMP}	V _{CC} ramp time		100	ms			
T _{RAMP}	V _{CC} ramp time	0.2		ms			

6.8 Typical Characteristics

The typical characteristics shown in this section apply to near-end eye measurements taken at nominal conditions. The eyes are measured with various pre-channel cable lengths applied at the input or post-channel cable lengths applied at the output of the TUSB211A as indicated.



Submit Document Feedback



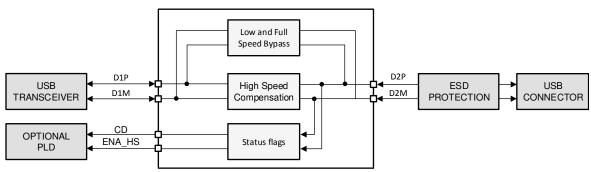
7 Detailed Description

7.1 Overview

The TUSB211A is a USB High-Speed (HS) signal conditioner designed to compensate for ISI signal loss in a transmission channel. TUSB211A has a patented design for USB Low Speed (LS) and Full Speed (FS) signals. It does not alter the signal characteristics. HS signals are compensated. The design is compatible with USB On-The-Go (OTG) and Battery Charging (BC) specifications.

Programmable signal gain through an external resistor permits fine tuning device performance to optimize signals. This helps pass USB HS electrical compliance tests at the connector. The TUSB211A allows application in series to cover longer distances, or high loss transmission paths. A maximum of 4 devices can be daisy-chained.

7.2 Functional Block Diagram



Copyright © 2018, Texas Instruments Incorporated

7.3 Feature Description

7.3.1 High-Speed EQ

The high-speed EQ (combination of edge boost and DC boost) improves the eye width for USB2.0 high-speed signals. It is direction independent and by that is compatible to OTG systems. The EQ pin is configuring the EQ strength with different values of pull down resistors to set 4 levels of EQ.

7.4 Device Functional Modes

7.4.1 Low-Speed (LS) Mode

TUSB211A automatically detects an LS connection and does not enable signal compensation. CD pin is asserted high but ENA_HS will be low.

7.4.2 Full-Speed (FS) Mode

TUSB211A automatically detects an FS connection and does not enable signal compensation. CD pin is asserted high but ENA HS will be low.

7.4.3 High-Speed (HS) Mode

TUSB211A automatically detects an HS connection and will enable signal compensation as determined by the external pull down resistance on its EQ pin.

CD pin and ENA HS pin are asserted high when high-speed EQ is active.

7.4.4 High-Speed Downstream Port Electrical Compliance Test Mode

TUSB211A will detect an HS compliance test fixture and enter the downstream port high-speed eye diagram test mode. CD pin will be low and ENA_HS pin is asserted high when TUSB211A is in HS eye compliance test mode.

If the RSTN pin is asserted low and de-asserted high while TUSB211A is operating in HS functional mode, then TUSB211A will transition to HS eye compliance test mode, the CD asserts low, and ENA_HS remains high. When all this occurs, signal compensation is enabled.



7.4.5 Shutdown Mode

TUSB211A can be disabled when its RSTN pin is asserted low. DP, DM traces are continuous through the device in shutdown mode. The USB channel is still fully operational, but there is neither signal compensation, nor any indication from the CD pin as to the status of the channel.

表 7-1. CD and ENA_HS Pins in Different Modes

MODE	CD	ENA_HS
Low-speed	HIGH	LOW
Full-speed	HIGH	LOW
High-speed	HIGH	HIGH
High-speed downstream port electrical test	LOW	HIGH
Shutdown	LOW	LOW

8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

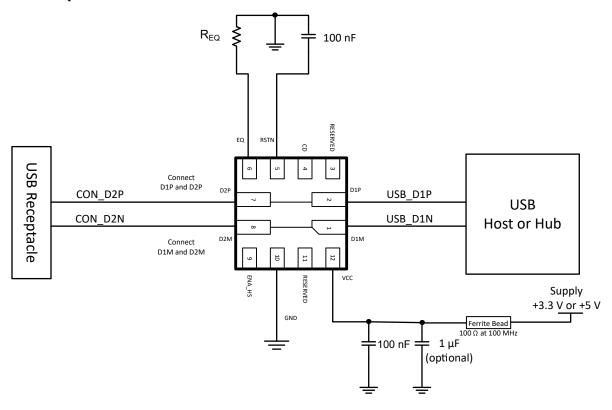
8.1 Application Information

The purpose of the TUSB211A is to restore the signal integrity of a USB High-speed channel up to the USB connector. The loss in signal quality stems from reduced channel bandwidth due to high loss PCB trace and other components that contribute a capacitive load. This can cause the channel to fail the USB near end eye mask. Proper use of the TUSB211A can help to pass this eye mask.

A secondary purpose is to use the CD pin of the TUSB211A to control other blocks on the customer platform, if so desired.

8.2 Typical Application

A typical application for TUSB211A is shown in 🗵 8-1. In this setup, D2P and D2M face the USB connector while D1P and D1M face the USB host. The orientation may be reversed [that is, D2 faces transceiver and D1 faces connector].



Copyright © 2023, Texas Instruments Incorporated

図 8-1. TUSB211A Reference Schematic



8.2.1 Design Requirements

TUSB211A requires a valid reset signal as described in the *Power Supply Recommendations* section. The capacitor at RSTN pin is not required if a micro controller drives the RSTN pin according to recommendations.

For this design example, use the parameters provided in 表 8-1.

表 8-1. Design Parameters for 3.3-V Supply With Low to Medium Loss System

PARAMETER				
V _{CC}			3.3 V ±10%	
I ² C support required in system (Yes/No)			No	
	R _{EQ}	EQ Level		
	0-Ω	0		
Edge and DC Boost	1.8 kΩ ±1%	1	EQ Level 0: $R_{EQ} = 0-\Omega$	
	3.6 kΩ ±1%	2		
	Do Not Install (DNI)	3		

⁽¹⁾ These parameters are starting values for a low to medium loss system. Further tuning might be required based on specific host or device as well as cable length and loss profile. These settings are not specific to a 3.3-V supply system and could be applicable to 5-V supply system as well.

8.2.2 Detailed Design Procedure

The ideal EQ setting is dependent upon the signal chain loss characteristics of the target platform. The recommendation is to start with EQ Level 0, and then increment to EQ Level 1, and so on.

For the TUSB211A to recognize any change to the EQ setting, the RSTN pin must be toggled. This is because the EQ pin is latched on power up and the pin is ignored thereafter.

Placement of the device is also dependent on the application goal. 表 8-2 describes TI recommendations.

表 8-2. Platform Placement Guideline

PLATFORM GOAL	SUGGESTED TUSB211A PLACEMENT				
Pass USB Near End Mask at the receptacle	Close to measurement point (connector)				
Pass USB Far End Eye Mask at the plug	Close to USB PHY				
Cascade multiple TUSB211As to improve device enumeration	Midway between each USB interconnect				

表 8-3. Table of Recommended Settings

EQ settings ⁽¹⁾ for channel loss							
Pre-channel cable length (Between USB PHY and TUSB211A)	EQ						
0-3 meter	Level 0						
2-5 meter	Level 1						
Post-channel cable length (Between TUSB211A and inter-connect)	EQ						
0-2 meter	Level 0						
1-4 meter	Level 1						

⁽¹⁾ These parameters are starting values for different cable lengths. Further tuning might be required based on specific host or device as well as cable length and loss profile.

8.2.2.1 Test Procedure to Construct USB High-Speed Eye Diagram

注

USB-IF certification tests for High-speed eye masks require the *mandated use* of the USB-IF developed test fixtures. These test fixtures do not require the use of oscilloscope probes. Instead they use SMA cables. More information can be found at the USB-IF Compliance Updates Page. It is located under the *Electrical Specifications* section, ID 86 dated March 2013.

Submit Document Feedback

Copyright © 2023 Texas Instruments Incorporated



The following procedure must be followed before using any oscilloscope compliance software to construct a USB High-speed Eye Mask:

8.2.2.1.1 For a Host Side Application

- 1. Configure the TUSB211A to the desired EQ setting.
- 2. Power on (or toggle the RSTN pin if already powered on) the TUSB211A.
- 3. Using SMA cables, connect the oscilloscope and the USB-IF host-side test fixture to the TUSB211A.
- 4. Enable the host to transmit USB TEST_PACKET.
- 5. Execute the oscilloscope USB compliance software.
- 6. Repeat the above steps to re-test TUSB211A with a different EQ setting (must reset to change).

8.2.2.1.2 For a Device Side Application

- 1. Configure the TUSB211A to the desired EQ setting.
- 2. Power on (or toggle the RSTN pin if already powered on) the TUSB211A.
- 3. Connect a USB host, the USB-IF device-side test fixture, and USB device to the TUSB211A. Ensure that the USB-IF device test fixture is configured to the 'INIT' position.
- 4. Allow the host to enumerate the device.
- 5. Enable the device to transmit USB TEST PACKET.
- 6. Using SMA cables, connect the oscilloscope to the USB-IF device-side test fixture and ensure that the device-side test fixture is configured to the 'TEST' position.
- 7. Execute the oscilloscope USB compliance software.
- 8. Repeat the above steps to re-test TUSB211A with a different EQ setting (must reset to change).



8.2.3 Application Curves

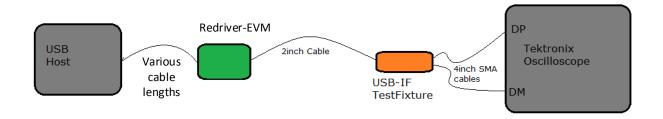
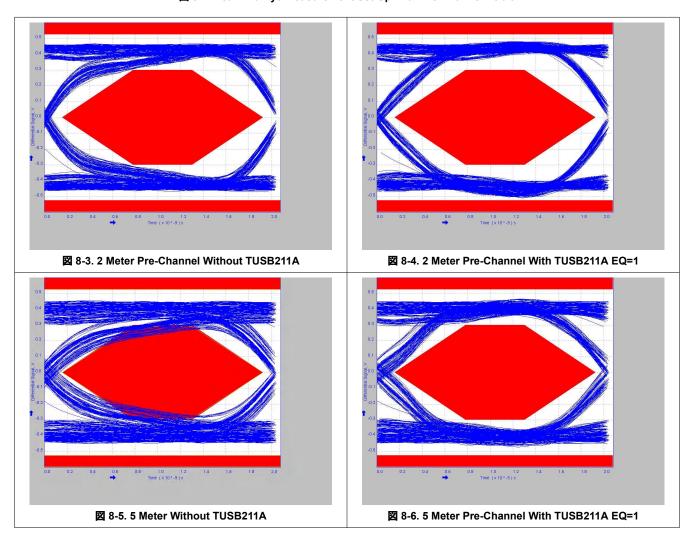
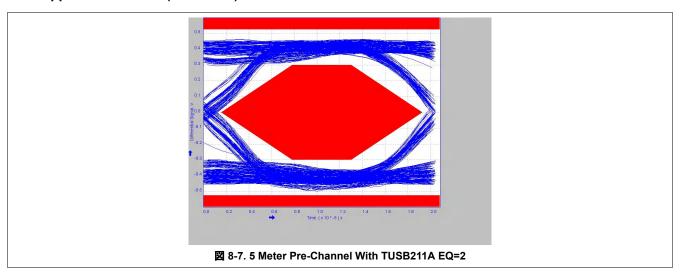


図 8-2. Near End Eye Measurement Set-Up With Pre-Channel Cable



8.2.3 Application Curves (continued)





8.2.3 Application Curves

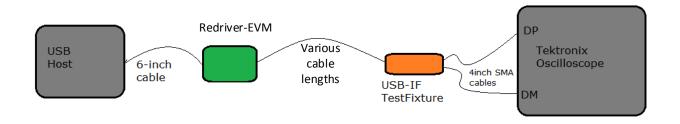
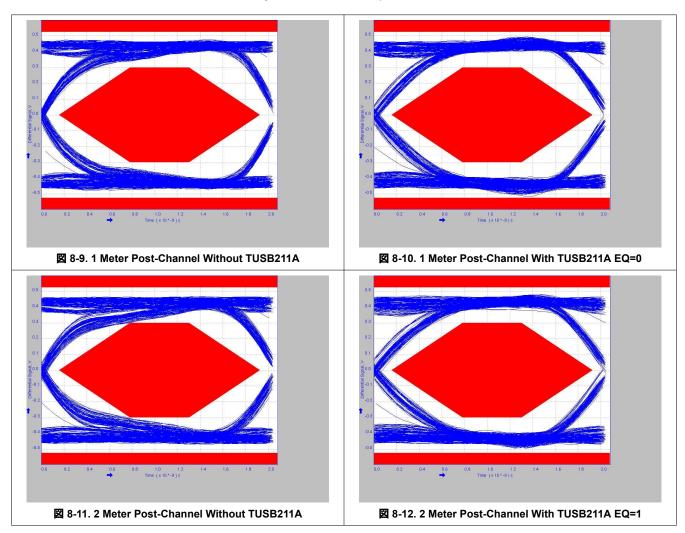
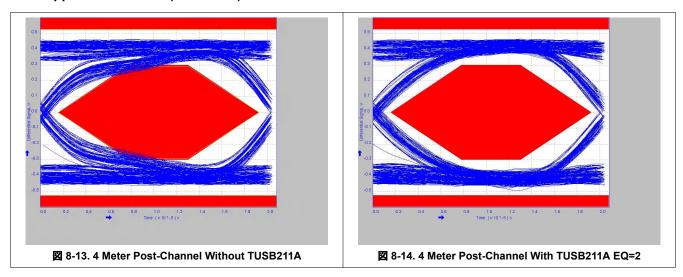


図 8-8. Near End Eye Measurement Set-Up With Post-Channel Cable



8.2.3 Application Curves (continued)



8.3 Power Supply Recommendations

On power up, the interaction of the RSTN pin and power on ramp could result in digital circuits not being set correctly. The device should not be enabled until the power on ramp has settled to the minimum recommended supply voltage or higher for a correct power on reset of the digital circuitry. If RSTN cannot be held low by microcontroller or other circuitry until the power on ramp has settled, then an external capacitor from the RSTN pin to GND is required to hold the device in the low power reset state.

The RC time constant should be larger than five times of the power on ramp time (0 to V_{CC}). With a typical internal pullup resistance of 500 k Ω , the recommended minimum external capacitance is calculated as:

$$[Ramp Time \times 5] \div [500 k\Omega] \tag{1}$$

8.4 Layout

8.4.1 Layout Guidelines

Although the land pattern has matched trace width to pad width, optimal impedance control is based on the user's own PCB stack-up. The recommendation is to maintain 90Ω differential routing underneath the device.



8.4.2 Layout Example

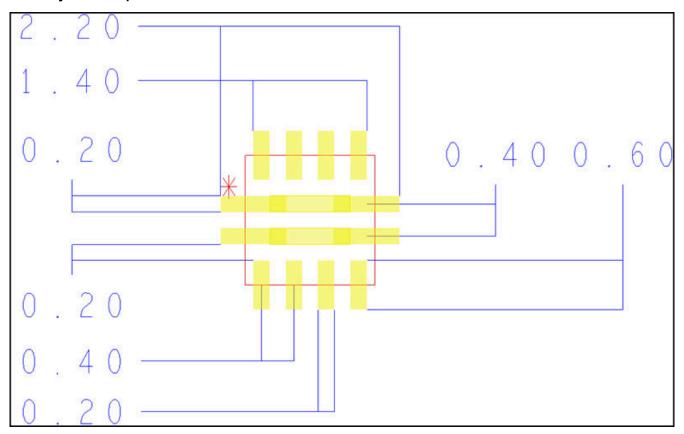


図 8-15. DP and DM Routing Underneath Device Package



9 Device and Documentation Support

9.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.com のデバイス製品フォルダを開いてください。「更新の通知を受 け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細 については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

9.2 サポート・リソース

TI E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接 得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得るこ とができます。

リンクされているコンテンツは、該当する貢献者により、現状のまま提供されるものです。これらは TI の仕様を構成するも のではなく、必ずしも TI の見解を反映したものではありません。TI の使用条件を参照してください。

9.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

9.4 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うこと を推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずか に変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

9.5 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 24-Oct-2023

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TUSB211AIRWBR	ACTIVE	X2QFN	RWB	12	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	1A	Samples
TUSB211ARWBR	ACTIVE	X2QFN	RWB	12	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	0 to 70	1A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

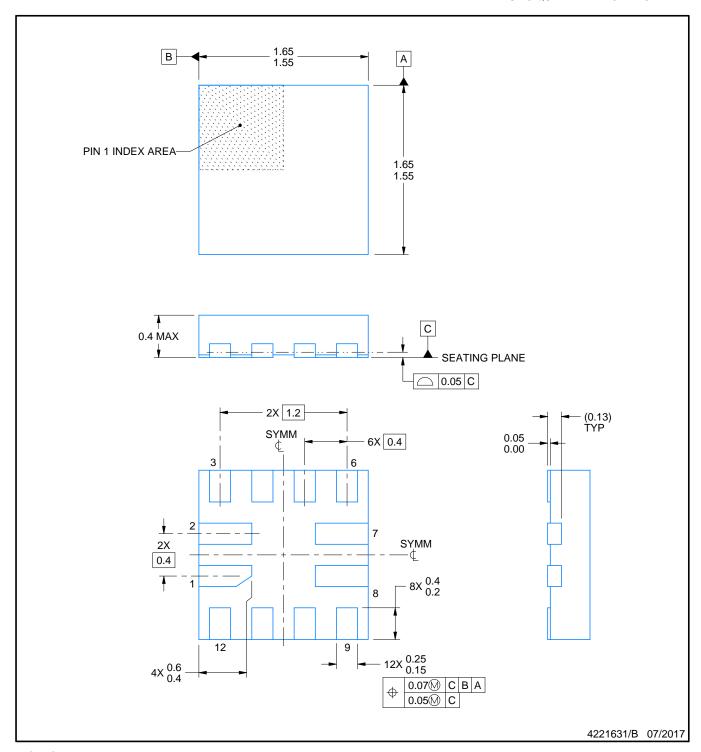


PACKAGE OPTION ADDENDUM

www.ti.com 24-Oct-2023



PLASTIC QUAD FLATPACK - NO LEAD



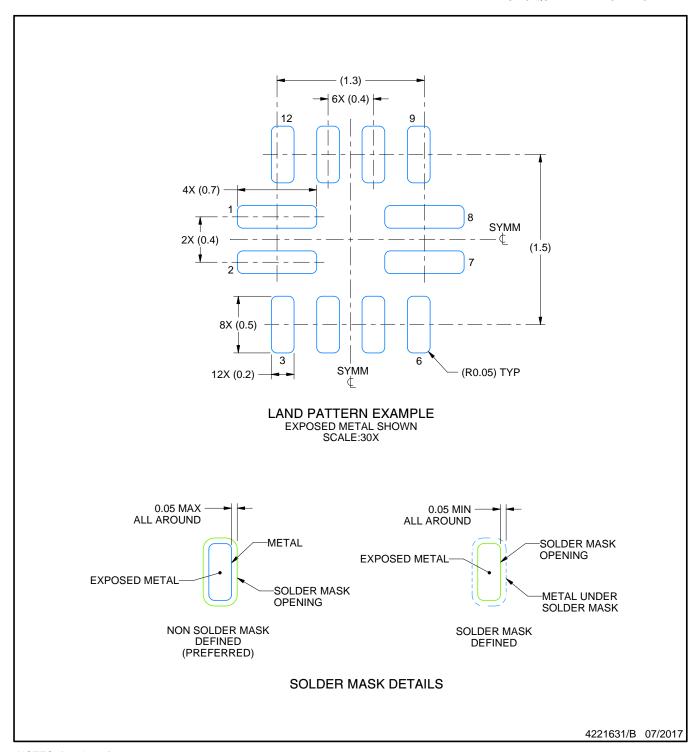
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



PLASTIC QUAD FLATPACK - NO LEAD

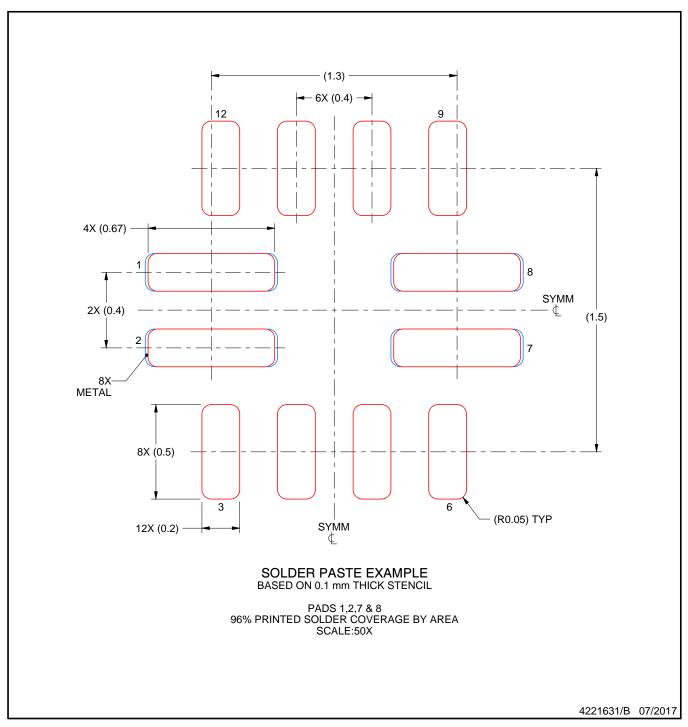


NOTES: (continued)

3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



重要なお知らせと免責事項

TI は、技術データと信頼性データ (データシートを含みます)、設計リソース (リファレンス・デザインを含みます)、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、TI 製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適した TI 製品の選定、(2) お客様のアプリケーションの設計、検証、試験、(3) お客様のアプリケーションに該当する各種規格や、その他のあら ゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとします。

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されている TI 製品を使用するアプリケーションの開発の目的でのみ、TI はその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。TI や第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、TI およびその代理人を完全に補償するものとし、TI は一切の責任を拒否します。

TIの製品は、TIの販売条件、または ti.com やかかる TI 製品の関連資料などのいずれかを通じて提供する適用可能な条項の下で提供されています。TI がこれらのリソースを提供することは、適用される TI の保証または他の保証の放棄の拡大や変更を意味するものではありません。

お客様がいかなる追加条項または代替条項を提案した場合でも、TIはそれらに異議を唱え、拒否します。

郵送先住所:Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2024, Texas Instruments Incorporated